IN THE SPECIFICATION

Please rewrite the paragraphs beginning on page 21, line 6, and ending on page 22, line 13, as follows:

Figs. 6A to 6H show a manufacturing method of the mirror section 2 used in the optical path control apparatus in the first embodiment. As shown in Fig. 6A, a silicon wafer 6 has the diameter of 6 inches, the crystal orientation of the (100) plane, and the thickness of 1 mm. Thermal oxidation films 7 are formed on the both sides of the silicon wafer to have the thickness of 1 μm. Next, as shown in Fig. 6B, a photoresist layer 8 is coated on one side of thermal oxidation films 7 to have the thickness of 5 μm. After exposure is carried out through a predetermined mask, development, rinsing by water, and patterning are carried out to form a first opening 9 in the photoresist layer 8. The first opening 9 has the shape of 100 μm × 70 μm. The photoresist layer 8 with the first opening 9 is immersed in buffered fluoric acid so as to etch thermal oxidation film 7 on the surface of the silicon wafer 6.

Next, as shown in Fig. 6C, after water-rinsing, the photoresist layer 8 is removed with solvent and is rinsed. Thus, a second opening 11 is formed in the thermal oxidation film 7 so that an exposed surface 12 is formed on the silicon wafer 6. As shown in Fig. 6D, the exposed surface of silicon wafer 6 through the second opening 11 is subjected to anisotropic etching with potassium hydroxide solution. Thus, a concave section 13 is formed to have the crystal orientation of the (111) plane and a square pyramid cross section. Then, as shown in Fig. 6E, the whole of thermal oxidation film 7 on the side of the silicon wafer 6 where the concave section 13 is formed is etched with the buffered fluoric acid. Here, as shown in Fig. 7A, a convex section 14 may be formed on the silicon wafer 6 as a die and the concave section 13 may be formed in the convex section 14, considering the installation.